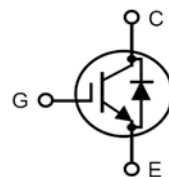


XPT™ 650V IGBT GenX4™ w/ Sonic Diode

IXXH60N65B4H1

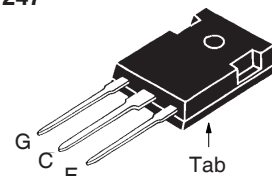


Extreme Light Punch Through
IGBT for 5-30 kHz Switching

$$\begin{aligned} V_{CES} &= 650V \\ I_{C110} &= 60A \\ V_{CE(sat)} &\leq 2.2V \\ t_{fi(typ)} &= 43ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 175°C	650	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 175°C , $R_{GE} = 1M\Omega$	650	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	145	A
I_{C110}	$T_C = 110^\circ\text{C}$	60	A
I_{F110}	$T_C = 110^\circ\text{C}$	47	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	265	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ\text{C}$, $R_G = 5\Omega$ Clamped Inductive Load	$I_{CM} = 120$ @ $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 360V$, $T_J = 150^\circ\text{C}$ $R_G = 82\Omega$, Non Repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	536	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque	1.13/10	Nm/lb.in
Weight		6	g

TO-247



G = Gate C = Collector
E = Emitter Tab = Collector

Features

- Optimized for 5-30kHz Switching
- Square RBSOA
- Anti-Parallel Sonic Diode
- Short Circuit Capability
- International Standard Package

Advantages

- High Power Density
- Extremely Rugged
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$, $V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ\text{C}$			25 μA 3 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 60A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ\text{C}$		1.8 2.1	2.2 V V

Symbol Test Conditions
 $(T_J = 25^\circ\text{C Unless Otherwise Specified})$
Characteristic Values
Min. Typ. Max.

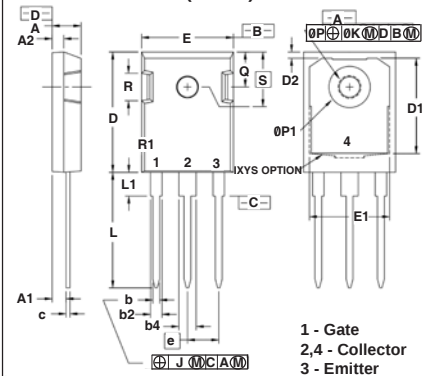
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	17	28	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		2590	pF
C_{oes}			310	pF
C_{res}			40	pF
$Q_{g(on)}$	$I_C = 60\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		86	nC
Q_{ge}			22	nC
Q_{gc}			35	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 60\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$ Note 2		19	ns
t_{ri}			80	ns
E_{on}			3.2	mJ
$t_{d(off)}$			107	ns
t_{fi}			43	ns
E_{off}			1.1	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 60\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$ Note 2		20	ns
t_{ri}			74	ns
E_{on}			4.2	mJ
$t_{d(off)}$			120	ns
t_{fi}			88	ns
E_{off}			1.8	mJ
R_{thJC}				0.28 $^\circ\text{C/W}$
R_{thCS}		0.21		$^\circ\text{C/W}$

Reverse Sonic Diode (FRD)
Symbol Test Conditions
 $(T_J = 25^\circ\text{C Unless Otherwise Specified})$
Characteristic Values
Min. Typ. Max.

V_F	$I_F = 30\text{A}, V_{GE} = 0\text{V}, \text{Note 1}$	$T_J = 150^\circ\text{C}$	1.5	2.5 V
I_{RM}	$I_F = 30\text{A}, V_{GE} = 0\text{V},$ $-di_F/dt = 900\text{A}/\mu\text{s}, V_R = 300\text{V}$	$T_J = 150^\circ\text{C}$	25	A
t_{rr}		$T_J = 150^\circ\text{C}$	78	ns
R_{thJC}				0.60 $^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

TO-247 (IXXH) Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
ØP	.140	.144	3.55	3.65
ØP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242 BSC		6.15 BSC	

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

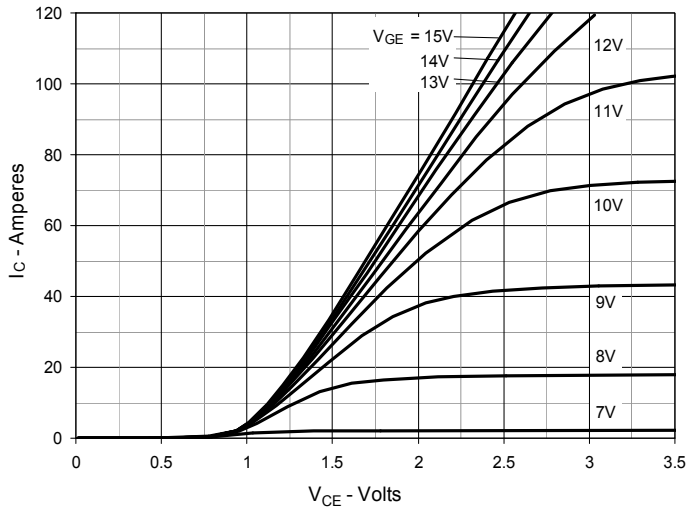
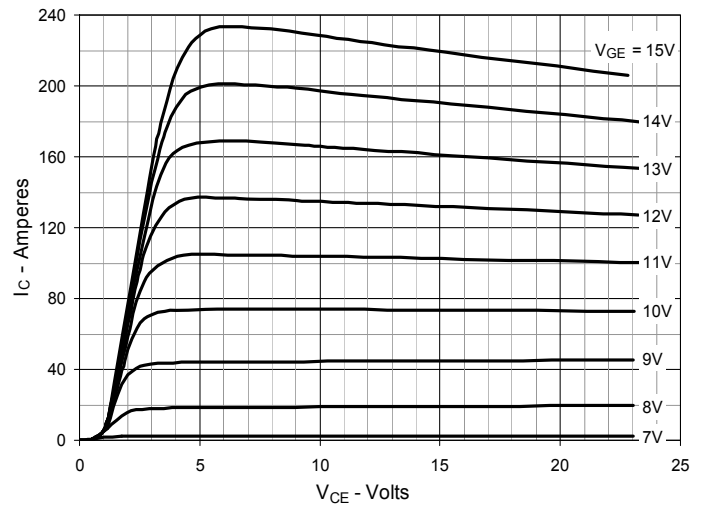
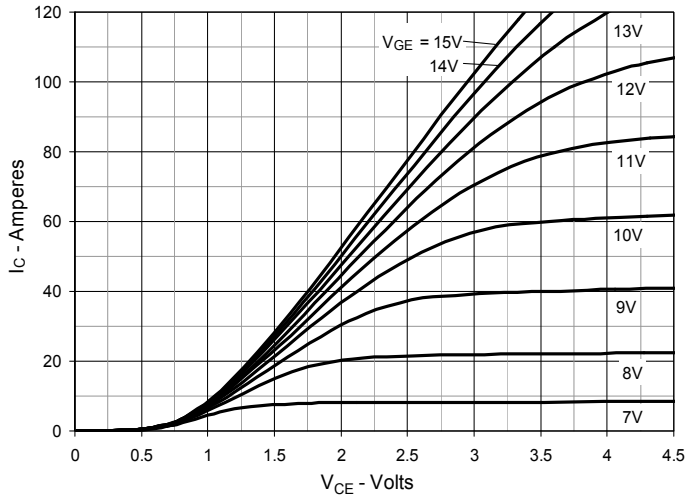
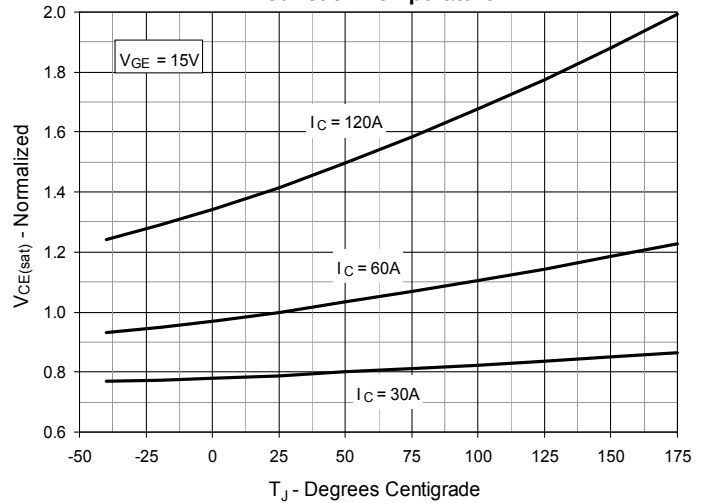
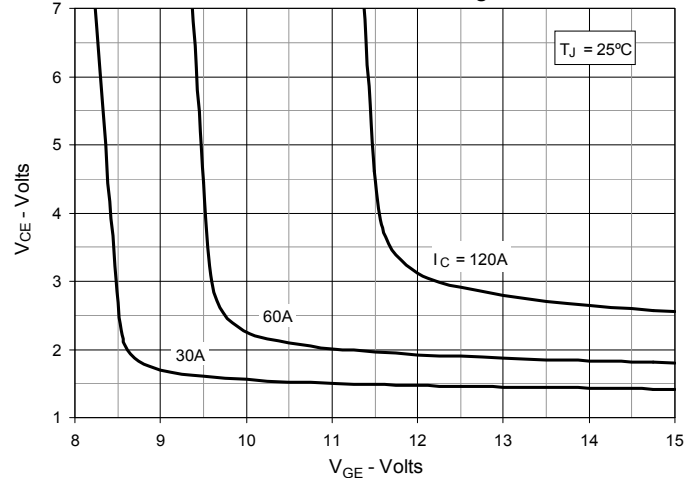
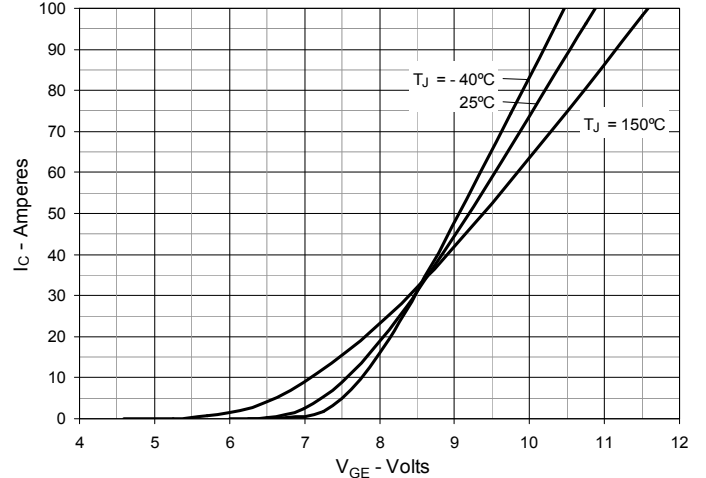
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

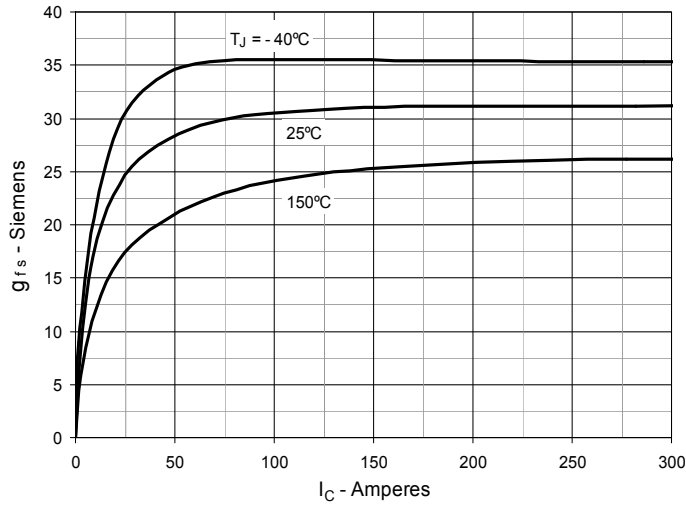


Fig. 8. Gate Charge

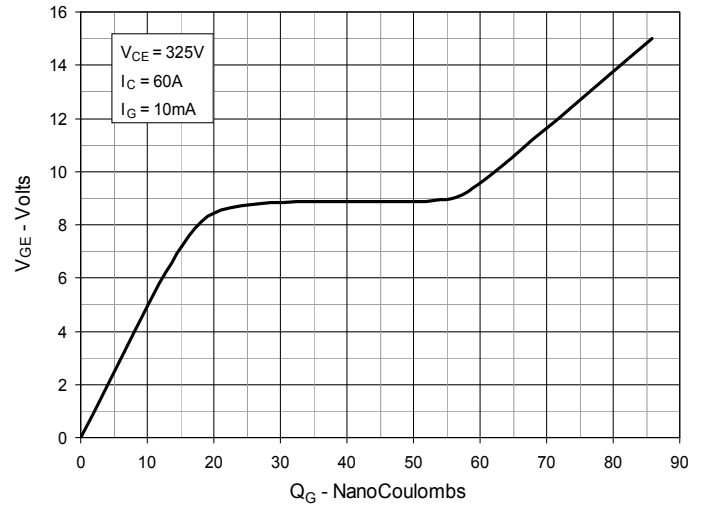


Fig. 9. Capacitance

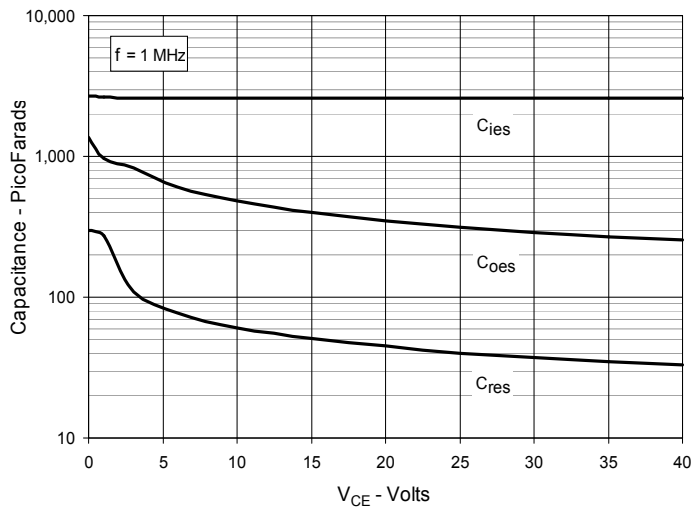


Fig. 10. Reverse-Bias Safe Operating Area

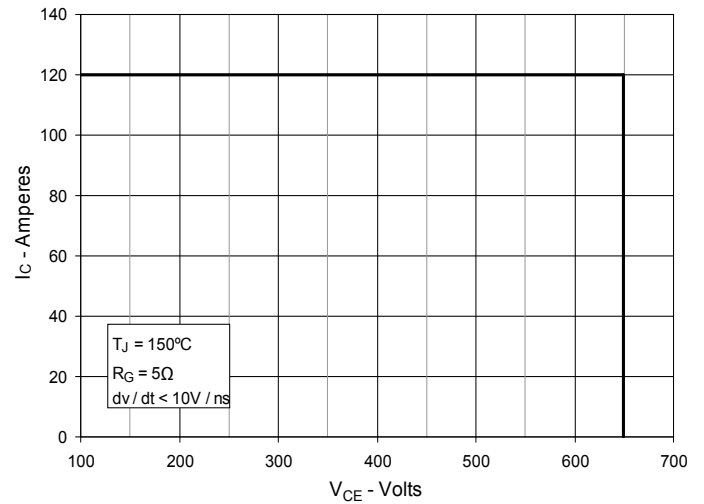


Fig. 11. Maximum Transient Thermal Impedance (IGBT)

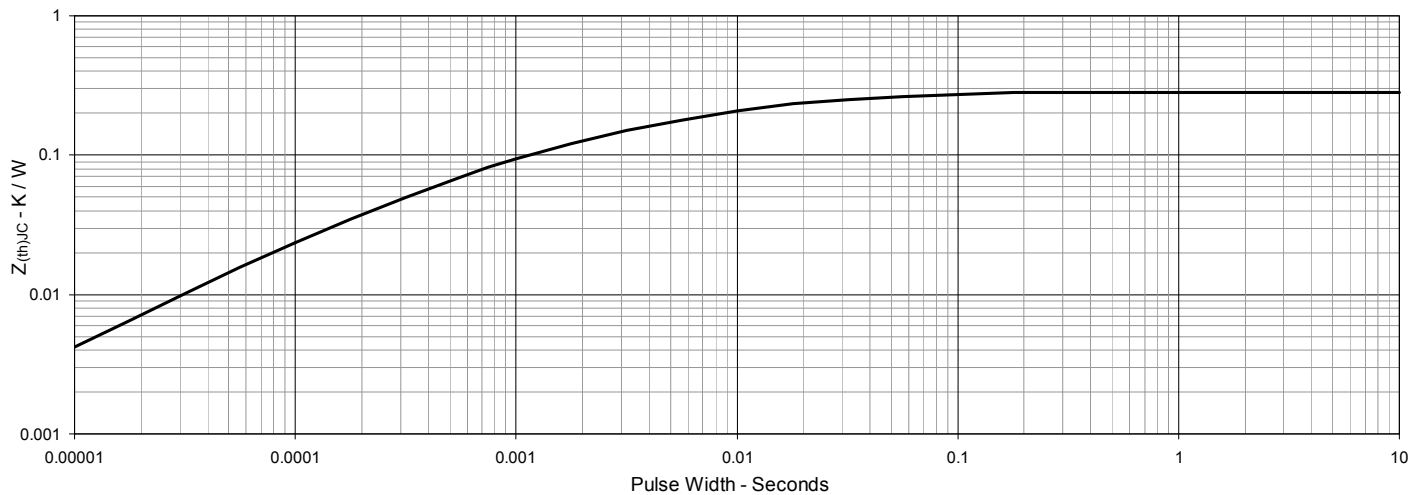


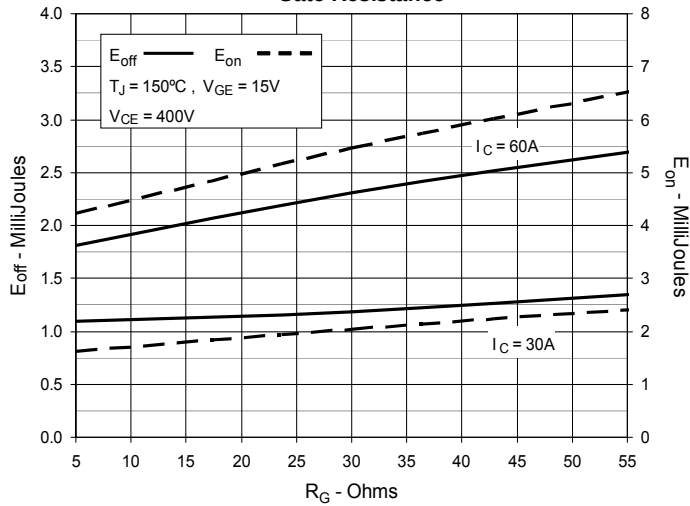
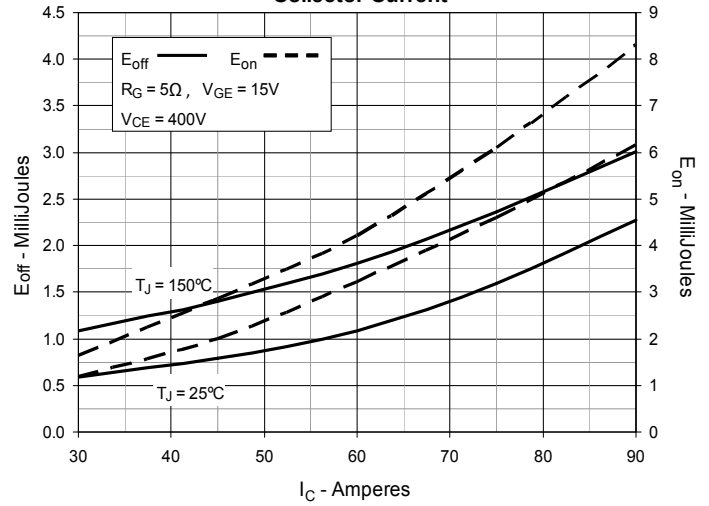
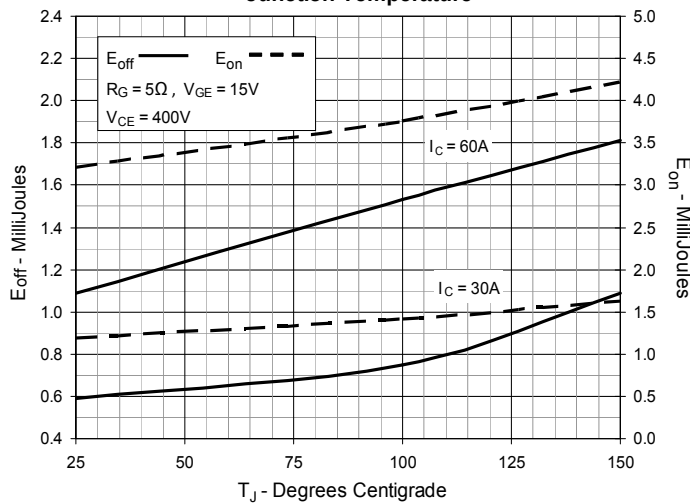
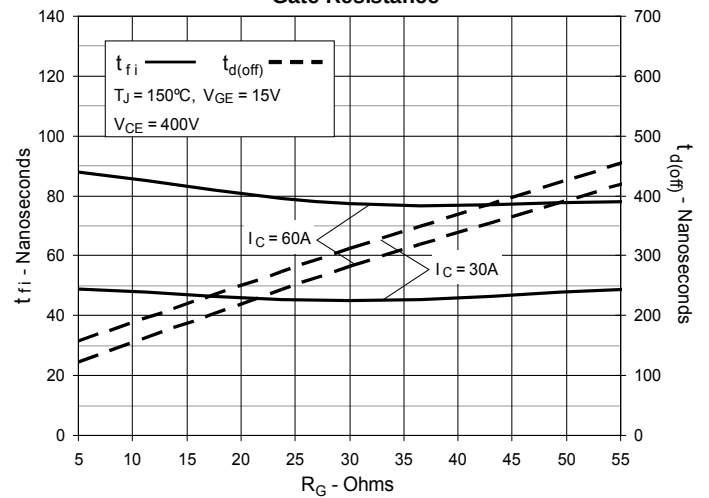
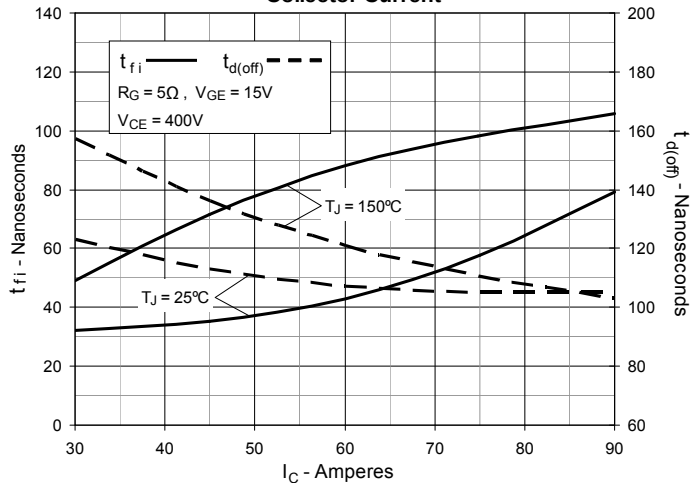
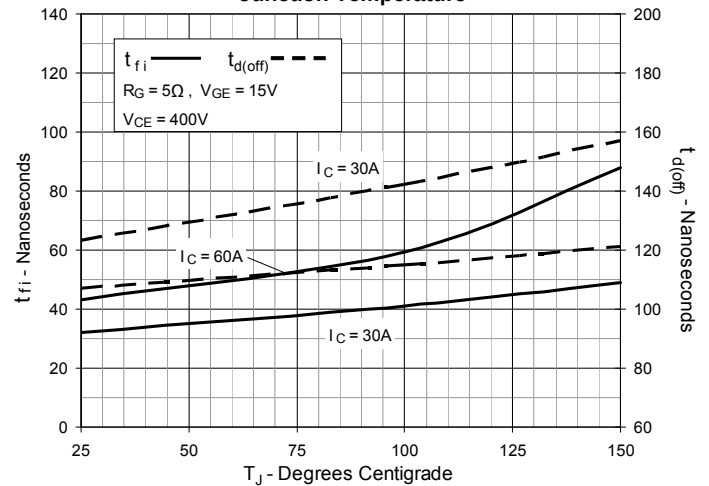
Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 13. Inductive Switching Energy Loss vs. Collector Current

Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature


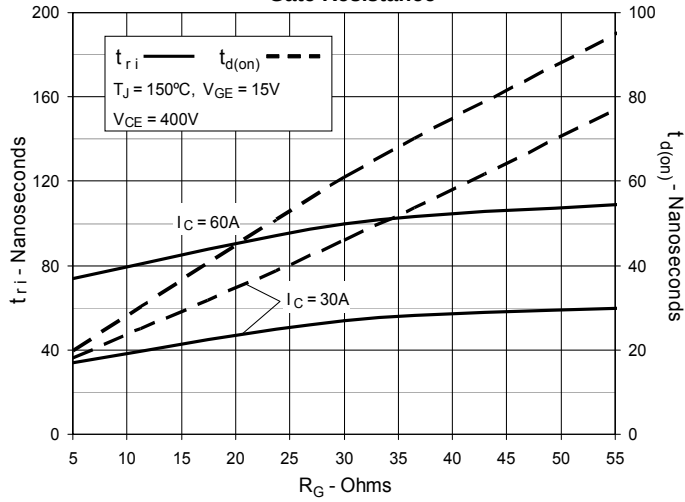
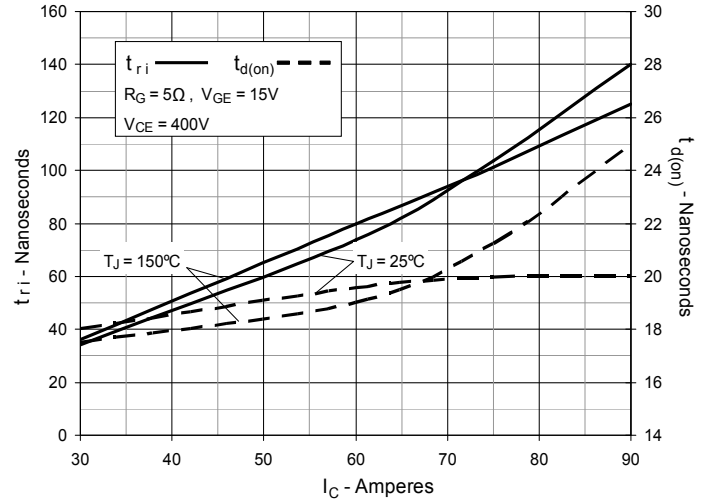
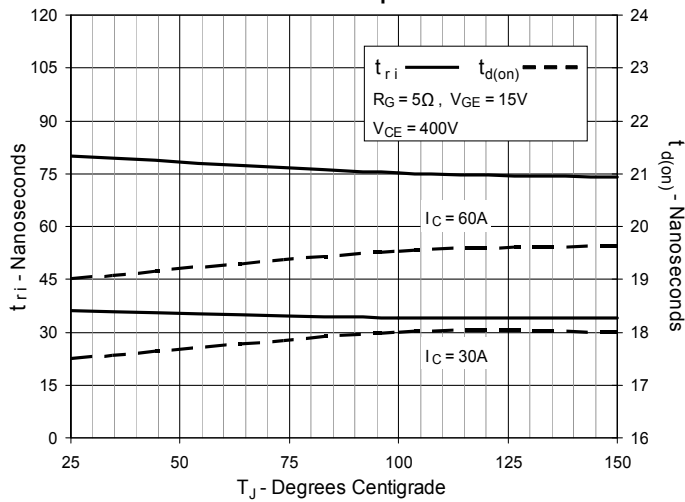
Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature


Fig. 21. Forward Current vs. Forward Voltage

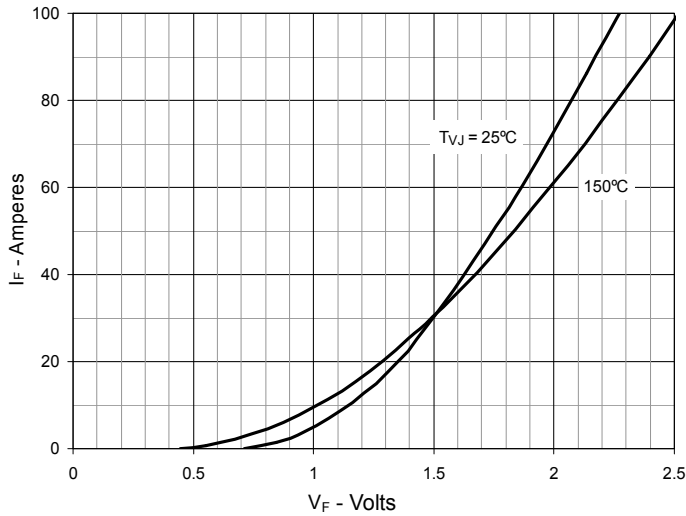


Fig. 22. Reverse Recovery Charge Q_{RR} vs. $-di_F/dt$

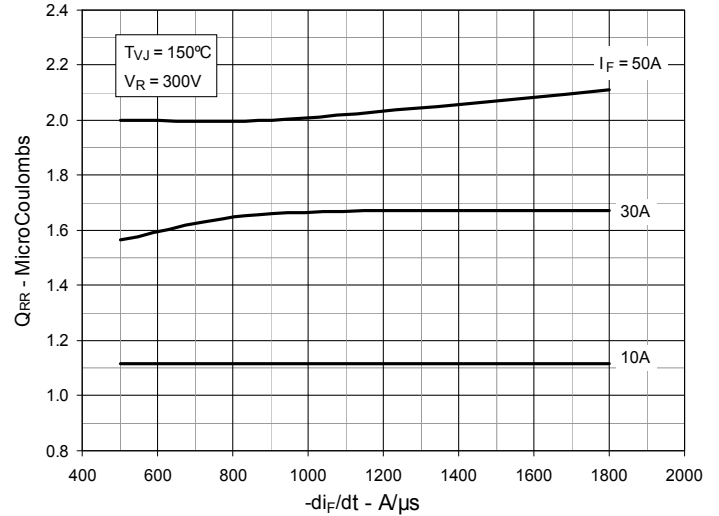


Fig. 23. Peak Reverse Current I_{RM} vs. $-di_F/dt$

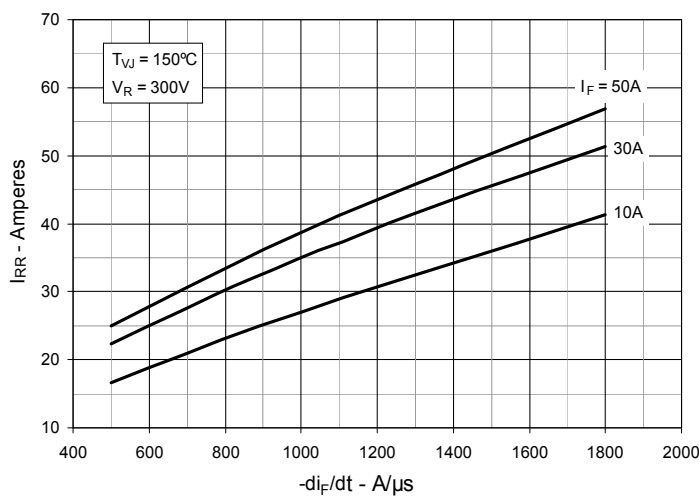


Fig. 24. Recover Time t_{RR} vs. $-di_F/dt$

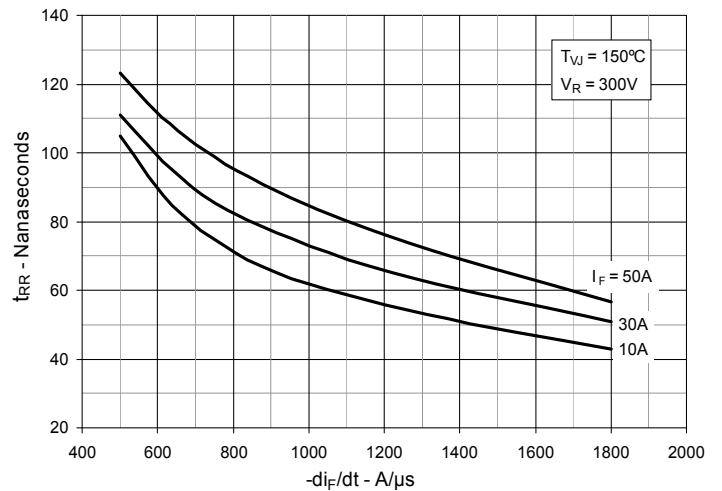


Fig. 25. Recovery Energy E_{REC} vs. $-di_F/dt$

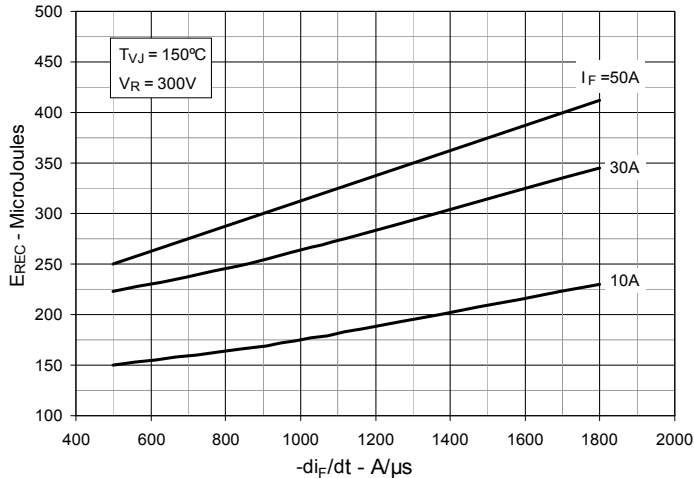


Fig. 26. Dynamic Parameters Q_{RR} , I_{RM} vs. Virtual Junction Temperature T_{VJ}

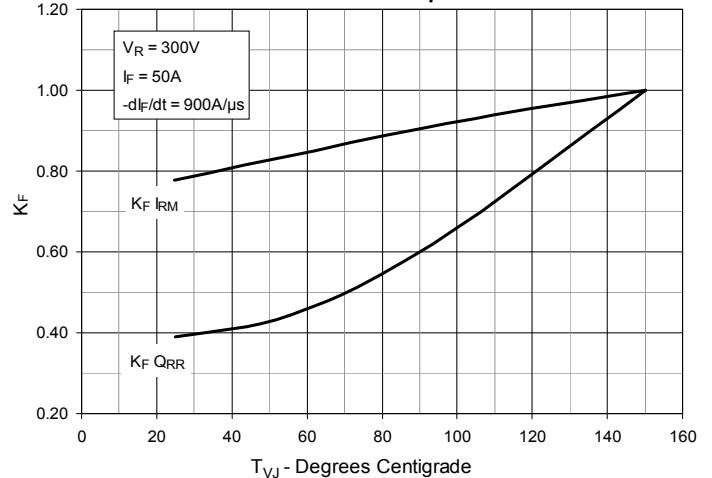


Fig. 27. Maximum Transient Thermal Impedance (Diode)

